

NMOS 256K (32K x 8) UV EPROM

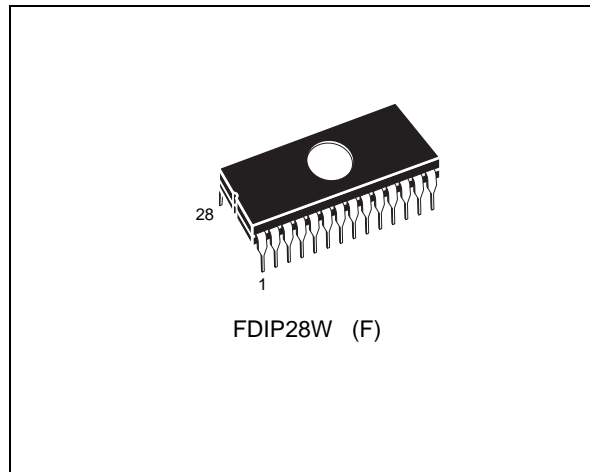
DATA BRIEFING

- FAST ACCESS TIME: 170ns
- EXTENDED TEMPERATURE RANGE
- SINGLE 5V SUPPLY VOLTAGE
- LOW STANDBY CURRENT: 40mA max
- TTL COMPATIBLE DURING READ and PROGRAM
- FAST PROGRAMMING ALGORITHM
- ELECTRONIC SIGNATURE
- PROGRAMMING VOLTAGE: 12V

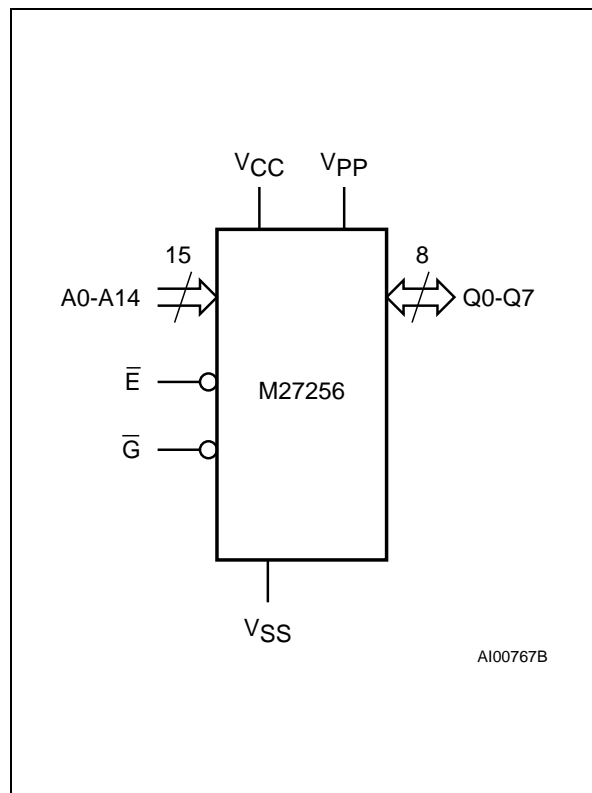
DESCRIPTION

The M27256 is a 262,144 bit UV erasable and electrically programmable memory EPROM. It is organized as 32.768 words by 8 bits.

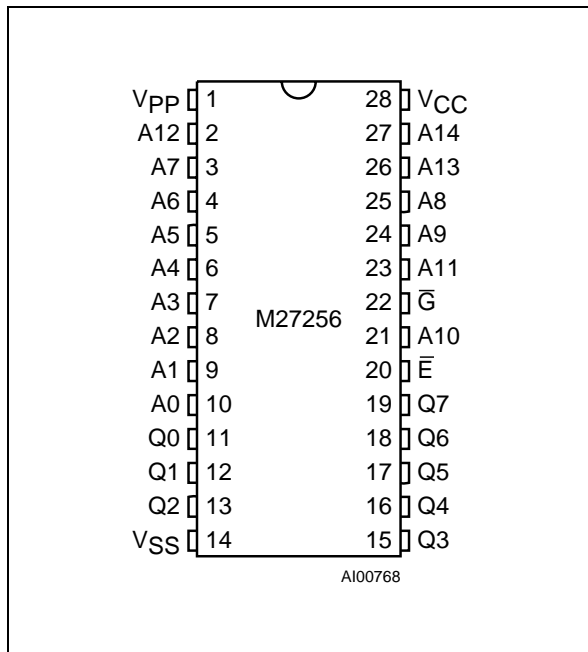
The M27256 is housed in a 28 pin Window Ceramic Frit-Seal Dual-in-Line package. The transparent lid allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written to the device by following the programming procedure.



Logic Diagram



DIP Pin Connections



Signal Names

A0 - A14	Address Inputs
Q0 - Q7	Data Outputs
\bar{E}	Chip Enable
\bar{G}	Output Enable
V _{PP}	Program Supply
V _{CC}	Supply Voltage
V _{SS}	Ground

Ordering Information Scheme

For a list of available options refer to the current Memory Shortform catalogue. For further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.

Example: M27256 -1 F 1

Speed and V_{CC} Tolerance	-1	F	1
-1	170ns, 5V ±5%		
-2	200ns, 5V ±5%		
blank	250ns, 5V ±5%		
-3	300ns, 5V ±5%		
-4	400ns, 5V ±5%		
-20	200ns, 5V ±10%		
-25	250ns, 5V ±10%		
Package	F		
	FDIP28W		
Temp. Range	1		
	0 to 70 °C		
	6		
	-40 to 85 °C		